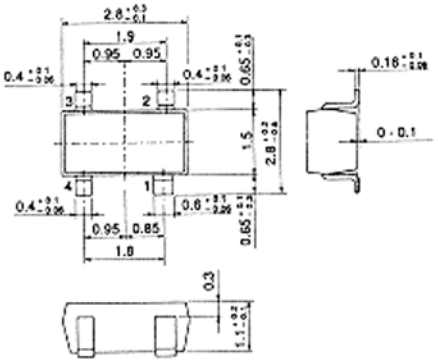
HITACHI

查询"3SK154"供应商

3SK154

SILICON N-CHANNEL DUAL GATE MOS FET

VHF AMPLIFIER
VHF TV TUNER RF AMPLIFIER



(MPAK-4)

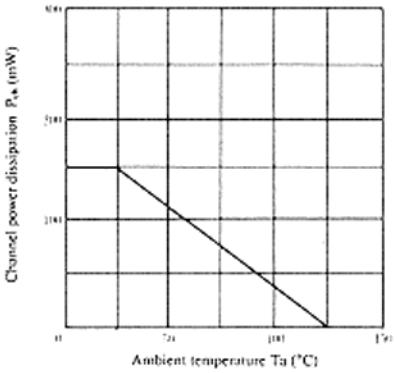
1. Source
2. Gate 1
3. Gate 2
4. Drain

(Dimensions in mm)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	3SK154	Unit
Drain to source voltage	V_{DSX}	15	V
Gate 1 to source voltage	V_{G1S}	±8	V
Gate 2 to source voltage	V_{G2S}	±8	V
Drain current	I_D	35	mA
Channel power dissipation	P_{ch}	150	mW
Channel temperature	T_{ch}	125	°C
Storage temperature	T_{stg}	−55 to +125	°C

MAXIMUM CHANNEL POWER DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Drain to source breakdown voltage	$V_{(BR)DSX}$	$V_{G1S} = V_{G2S} = -8V$, $I_D = 200\mu A$	15	—	—	V
Gate 1 to source breakdown voltage	$V_{(BR)G1SS}$	$I_{G1} = \pm 10\mu A$, $V_{G2S} = V_{DS} = 0$	±8	—	±20	V
Gate 2 to source breakdown voltage	$V_{(BR)G2SS}$	$I_{G2} = \pm 10\mu A$, $V_{G1S} = V_{DS} = 0$	±8	—	±20	V
Gate 1 cutoff current	I_{G1SS}	$V_{G1S} = \pm 8V$, $V_{G2S} = V_{DS} = 0$	—	—	±100	nA
Gate 2 cutoff current	I_{G2SS}	$V_{G2S} = \pm 8V$, $V_{G1S} = V_{DS} = 0$	—	—	±100	nA
Gate 1 to source cutoff voltage	$V_{G1S(off)}$	$V_{DS} = 10V$, $V_{G2S} = 3V$, $I_D = 100\mu A$	—	—	−2	V
Gate 2 to source cutoff voltage	$V_{G2S(off)}$	$V_{DS} = 10V$, $V_{G1S} = 3V$, $I_D = 100\mu A$	—	—	−2	V
Drain current	I_{DSS}	$V_{DS} = 6V$, $V_{G2S} = 3V$, $V_{G1S} = 0$	—	—	30	mA
Forward transfer admittance	$\lvert y_{fs} \rvert$	$V_{DS} = 6V$, $V_{G2S} = 3V$, $I_D = 10mA$, $f = 1kHz$	15	—	—	mS
Input capacitance	C_{iss}	$V_{DS} = 6V$, $V_{G2S} = 3V$, $I_D = 10mA$, $f = 1MHz$	—	4.5	—	pF
Output capacitance	C_{oss}		—	3	—	pF
Reverse transfer capacitance	C_{rss}		—	0.03	—	pF
Power gain	PG	$V_{DS} = 6V$, $V_{G2S} = 3V$, $I_D = 10mA$, $f = 200MHz$	22	—	—	dB
Noise figure	NF		—	—	3	dB

* Marking is [IZ–].

■ See characteristic curves of 3SK96.